

General Description

OST40N65PUXF uses advanced Oriental-Semi's patented Trident-Gate Bipolar Transistor (TGBT™) technology to provide extremely low $V_{CE(sat)}$, low gate charge, and excellent switching performance. This device is suitable for mid to high range switching frequency converters.

Features

- Advanced TGBT™ technology
- Excellent conduction and switching loss
- Excellent stability and uniformity
- Fast and soft antiparallel diode



Applications

- Induction converters
- Uninterruptible power supplies

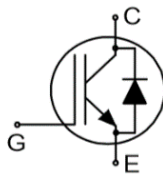
Key Performance Parameters

Parameter	Value	Unit
$V_{CES, min} @ 25\text{ °C}$	650	V
Maximum junction temperature	175	°C
$I_C, pulse$	160	A
$V_{CE(sat), typ} @ V_{GE}=15\text{ V}$	1.95	V
Q_g	44	nC

Marking Information

Product Name	Package	Marking
OST40N65PUXF	TO220	OST40N65PUX

Package & Pin Information



Absolute Maximum Ratings at $T_{vj}=25\text{ °C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Collector emitter voltage	V_{CES}	650	V
Gate emitter voltage	V_{GES}	± 20	V
Transient gate emitter voltage, $T_P \leq 10\ \mu s$, $D < 0.01$		± 30	V
Continuous collector current ¹⁾ , $T_C=25\text{ °C}$	I_C	56	A
Continuous collector current ¹⁾ , $T_C=100\text{ °C}$		40	A
Pulsed collector current ²⁾ , $T_C=25\text{ °C}$	$I_{C, pulse}$	160	A
Diode forward current ¹⁾ , $T_C=25\text{ °C}$	I_F	56	A
Diode forward current ¹⁾ , $T_C=100\text{ °C}$		40	A
Diode pulsed current ²⁾ , $T_C=25\text{ °C}$	$I_{F, pulse}$	160	A
Power dissipation ³⁾ , $T_C=25\text{ °C}$	P_D	313	W
Power dissipation ³⁾ , $T_C=100\text{ °C}$		157	W
Operation and storage temperature	T_{stg}, T_{vj}	-55 to 175	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
IGBT thermal resistance, junction-case	$R_{\theta JC}$	0.48	°C/W
Diode thermal resistance, junction-case	$R_{\theta JC}$	0.7	°C/W
Thermal resistance, junction-ambient	$R_{\theta JA}$	40	°C/W

Electrical Characteristics at $T_{vj}=25\text{ °C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Collector-emitter breakdown voltage	$V_{(BR)CES}$	650			V	$V_{GE}=0\text{ V}$, $I_C=0.5\text{ mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		1.95	2.3	V	$V_{GE}=15\text{ V}$, $I_C=40\text{ A}$ $T_{vj}=25\text{ °C}$
			2.87		V	$V_{GE}=15\text{ V}$, $I_C=40\text{ A}$, $T_{vj}=125\text{ °C}$
			3.78		V	$V_{GE}=15\text{ V}$, $I_C=40\text{ A}$, $T_{vj}=175\text{ °C}$
Gate-emitter threshold voltage	$V_{GE(th)}$	3.0	4.0	5.0	V	$V_{CE}=V_{GE}$, $I_C=0.5\text{ mA}$
Diode forward voltage	V_F		2.65	3.0	V	$V_{GE}=0\text{ V}$, $I_F=40\text{ A}$ $T_{vj}=25\text{ °C}$
			1.90		V	$V_{GE}=0\text{ V}$, $I_F=40\text{ A}$, $T_{vj}=125\text{ °C}$
			1.68		V	$V_{GE}=0\text{ V}$, $I_F=40\text{ A}$, $T_{vj}=175\text{ °C}$
Gate-emitter leakage current	I_{GES}			100	nA	$V_{CE}=0\text{ V}$, $V_{GE}=20\text{ V}$
Zero gate voltage collector current	I_{CES}			10	μA	$V_{CE}=650\text{ V}$, $V_{GE}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{ies}		1799		pF	$V_{GE}=0\text{ V}$, $V_{CE}=25\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oes}		118		pF	
Reverse transfer capacitance	C_{res}		14		pF	
Turn-on delay time	$t_{d(on)}$		16		ns	$V_{GE}=15\text{ V}$, $V_{CC}=400\text{ V}$, $R_G=10\ \Omega$, $I_C=40\text{ A}$
Rise time	t_r		31		ns	
Turn-off delay time	$t_{d(off)}$		61		ns	
Fall time	t_f		27		ns	
Turn-on energy	E_{on}		1.01		mJ	
Turn-off energy	E_{off}		0.31		mJ	
Turn-on delay time	$t_{d(on)}$		15		ns	$V_{GE}=15\text{ V}$, $V_{CC}=400\text{ V}$, $R_G=10\ \Omega$, $I_C=20\text{ A}$
Rise time	t_r		13		ns	
Turn-off delay time	$t_{d(off)}$		73		ns	
Fall time	t_f		10		ns	
Turn-on energy	E_{on}		0.32		mJ	
Turn-off energy	E_{off}		0.15		mJ	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		44		nC	$V_{GE}=15\text{ V}$, $V_{CC}=520\text{ V}$, $I_C=40\text{ A}$
Gate-emitter charge	Q_{ge}		14		nC	
Gate-collector charge	Q_{gc}		15		nC	

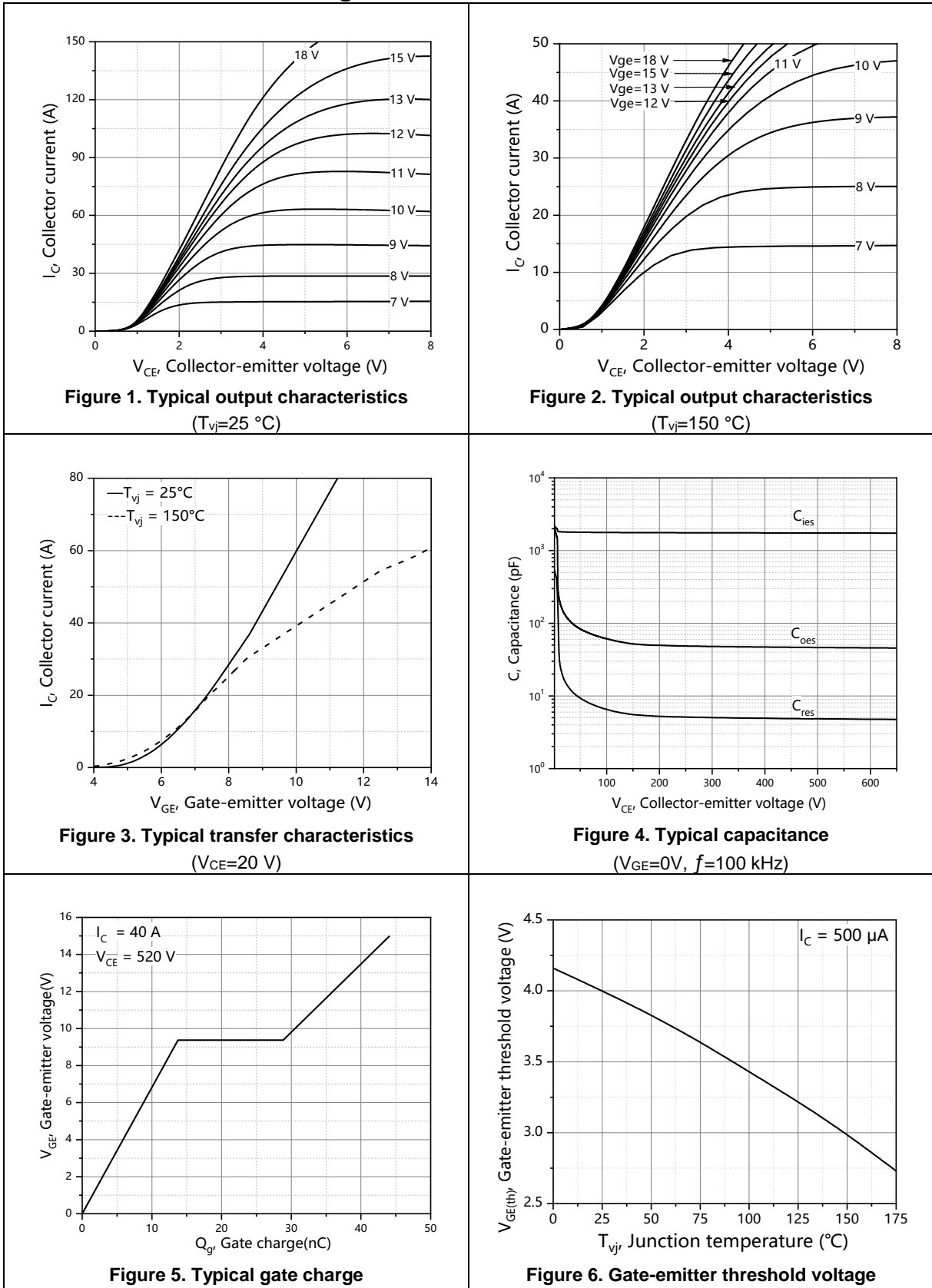
Body Diode Characteristics

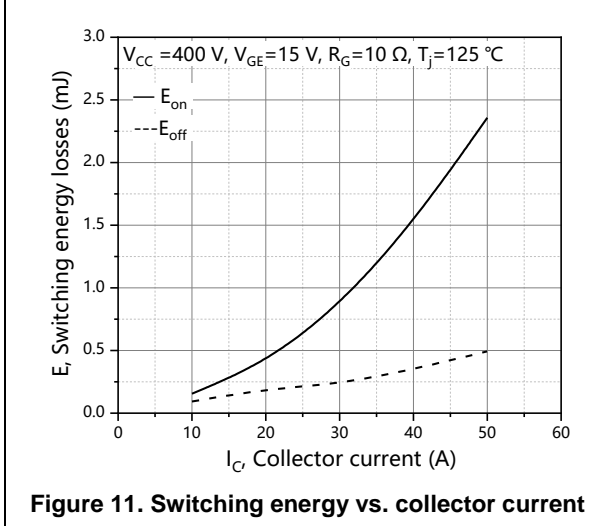
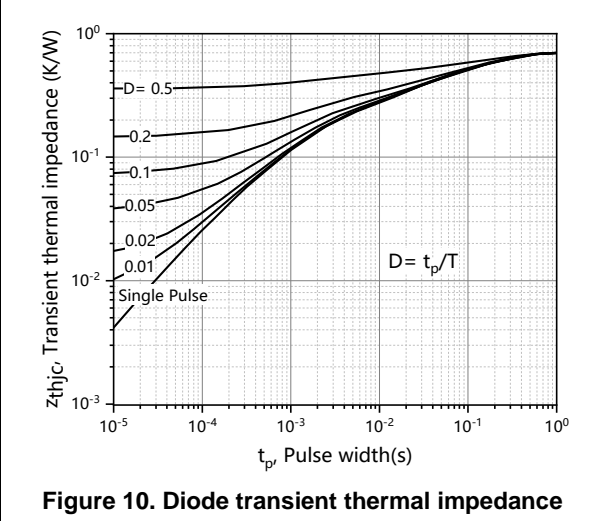
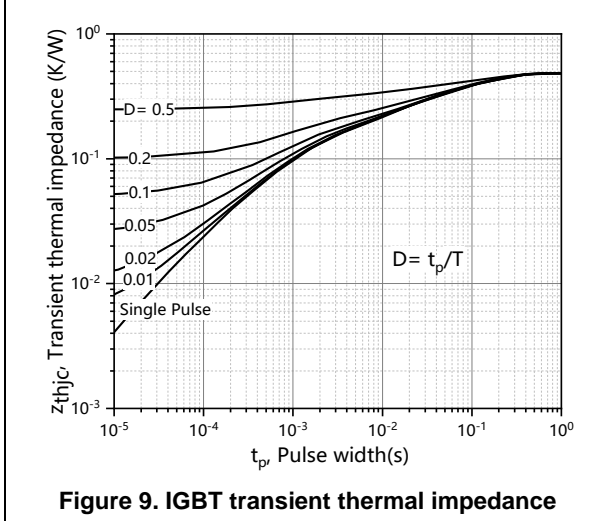
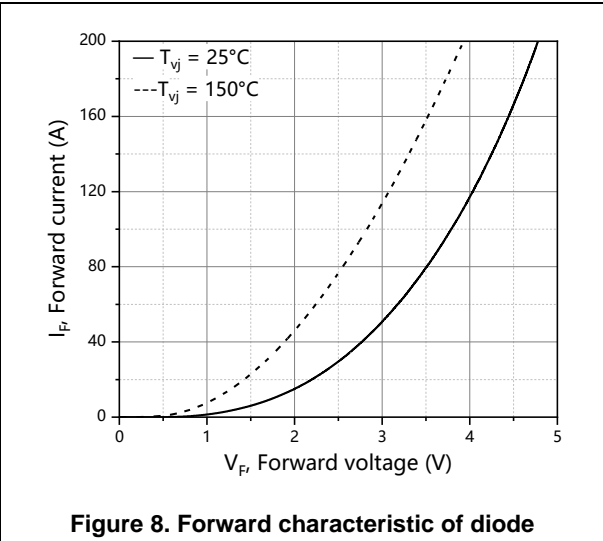
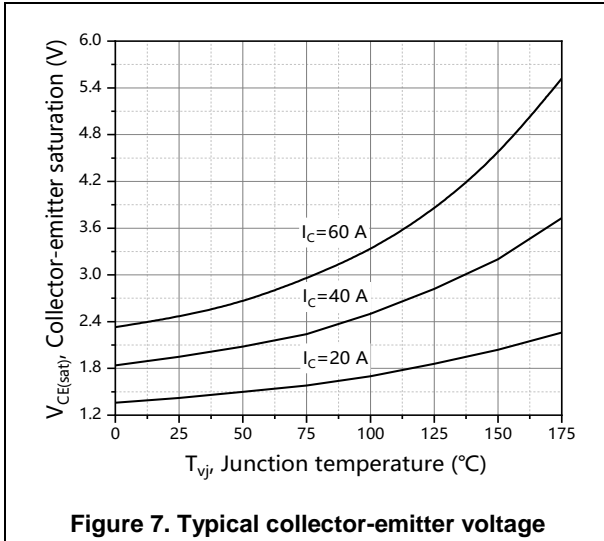
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode reverse recovery time	t_{rr}		103		ns	$V_R=400\text{ V}$, $I_F=40\text{ A}$, $di_F/dt=500\text{ A}/\mu\text{s}$ $T_{vj}=25\text{ }^\circ\text{C}$
Diode reverse recovery charge	Q_{rr}		0.18		μC	
Diode peak reverse recovery current	I_{rrm}		6		A	

Note

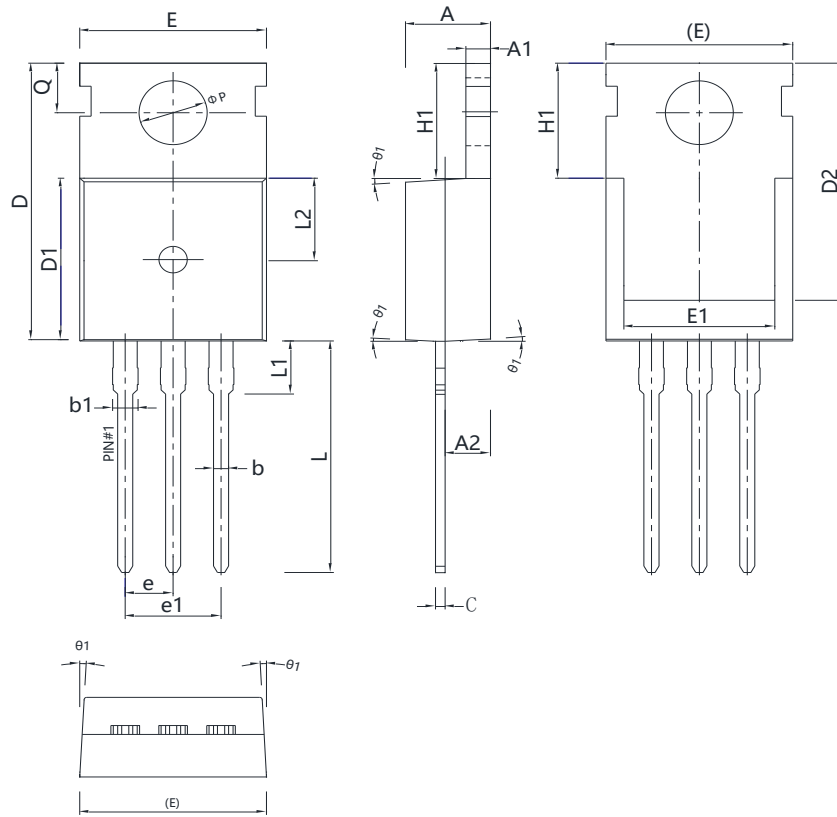
- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.

Electrical Characteristics Diagrams





Package Information



Symbol	mm		
	Min	Nom	Max
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	-	13.70
E	9.70	9.90	10.20
E1	7.80	8.00	8.20
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	-	-	3.50
L2	4.60 REF		
ΦP	3.55	3.60	3.65
Q	2.73	-	2.87
θ1	1°	3°	5°

Version : TO220-J package outline dimension

Ordering Information

Package Type	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220-J	50	20	1000	5	5000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OST40N65PUXF	TO220	yes	yes	yes

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